


 Cite this: *RSC Adv.*, 2017, 7, 10557

Correction: The polarization-dependent anisotropic Raman response of few-layer and bulk WTe_2 under different excitation wavelengths

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DOI: 10.1039/c7ra90007d

www.rsc.org/advances

 Correction for 'The polarization-dependent anisotropic Raman response of few-layer and bulk WTe_2 under different excitation wavelengths' by Qingjun Song *et al.*, *RSC Adv.*, 2016, 6, 103830–103837.

In part (d) of Fig. 4 of the original manuscript, and in the description of part (d) in the Fig. 4 caption, the wrong labels were given for the modes. The labels “ B_g ” and “ A_u ” should be “ B_u ” and “ A_g ”, respectively. The corrected Fig. 4 and its caption are shown below:

Additionally, in the Results and Discussion section, in the text below Fig. 4, two sentences should be revised as follows:

“For $E_{\text{las}} \approx 2.3$ eV, the excited electron will transit from the A_g valence band to A_u conductance band, and the corresponding polar plot is shown in Fig. 4(e), where the maximum (minimum) absorption corresponds to the perpendicular (parallel) relation between the incident polarization and a -axis”.

“To study the influence of electron–photon interaction on the anisotropic Raman scattering, we first assume the electron–phonon interaction (H_{e-ph}) in the Raman scattering is not polarization dependent”.

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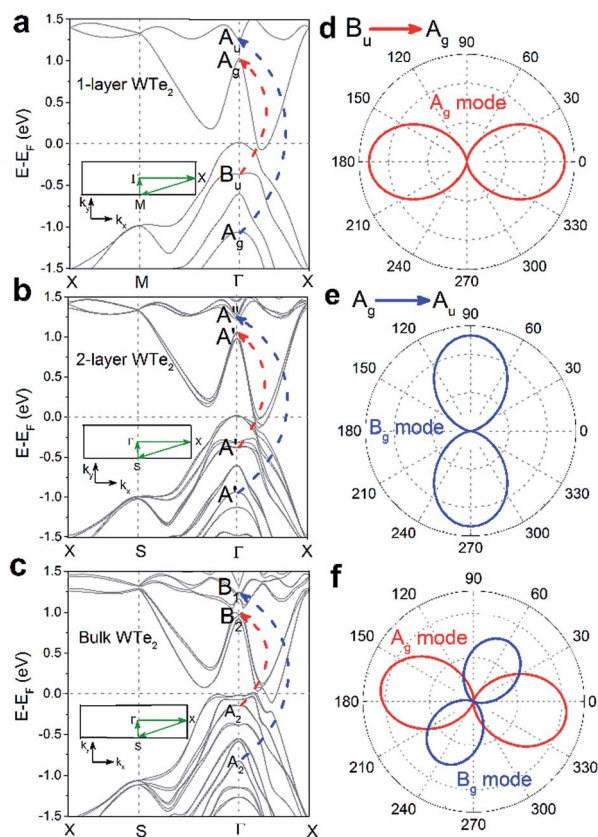


Fig. 4 (a–c) The calculated band structures of monolayer, bilayer and bulk WTe₂, respectively. The representative band symmetries at Γ point are labelled, and the insets are their 2D Brillouin zones. Calculated polarization dependence of the optical transition probability (d) from the B_u to A_g ($E_{\text{las}} \approx 1.5$ eV) and (e) from the A_g to A_u ($E_{\text{las}} \approx 2.3$ eV) in monolayer WTe₂, as indicated in (a). 0° corresponds to the W–W chain (a -axis) direction, the initial incident polarization and scattered polarization are along the a -axis ($\theta_0 = 0^\circ$). (f) The representative calculated polarization dependent intensities of A_g and B_g modes in monolayer WTe₂ with certain θ_0 ($\sim 15^\circ$).

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

